CTND2G08U3D

3V/1.8V, x8/x16 2G-BIT NAND FLASH

Documents title

2Gbit (256Mx8Bit, 128Mx16Bit) NAND FLASH

Revision History

Revision No.	History	Draft date	Remark
0.0	Initial Draft	Apr.05.2013	Preliminary
0.1	Added Data Retention 4bit /512byte ECC. Changed Read ID value 5th from 44h to 46h.	Aug.27.2014	
0.2	Added 63B, 67B FBGA Ball Assignments	Dec.01.2014	
0.3	Changed typical TPROG	Feb.11.2015	
0.4	Revised the 4th Read ID	Jun. 21. 2016	Final

FEATURES

■ x8/x16 I/O BUS

- NAND Interface
- ADDRESS / DATA Multiplexing

■ SUPPLY VOLTAGE

- VCC = 1.8/2.7/3.3 Volt core supply voltage for Program, Erase and Read operations

■ PAGE READ / PROGRAM

- x8 : (2048+64 spare) byte
- x16: (1024+32 spare) word page
- Synchronous Page Read Operation
- Random access : 25us (Max)
- Serial access : 45ns (1.8V)
  25ns (2.7/3.0V)
- Page program time : 300us (Typ)

■ PAGE COPY BACK

- Fast data copy without external buffering

■ CACHE PROGRAM

- Internal buffer to improve the program throughput

■ READ CACHE

■ LEGACY/ONFI 1.0 COMMAND SET

■ FAST BLOCK ERASE

- Block size :
  x8 : (128K + 4K) bytes x16: (64K+2K) words
- Block erase time : 2ms (Typ)

■ MEMORY CELL ARRAY

- x8 : (2K + 64) bytes x 64 pages x 2048 blocks
- x16: (1K + 32) words x 64 pages x 2048 blocks

■ ELECTRONIC SIGNATURE

- Manufacturer Code
- Device Code

■ STATUS REGISTER

■ HARDWARE DATA PROTECTION

■ DATA RETENTION

- Max cycling : 50K Program / Erase cycles
- Data retention : 10 Years(4bit/512byte ECC)

如需获取完整版规格书
请联系我司岳经理
电话：18138426570
微信二维码如下：

Linda